

INFORMATION DISCLOSURE

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Applicant(s): OOI et al.

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FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a
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	EP 0812485 B1	12/17/97	Europe	National Research Council Canada	n/a
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Examiner's Signature:

Date Considered: 9/21/02

Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered.

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